



ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _J =125 R _L =3.3k	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	15	mA
				20	
I _H	I _T =500mA		MAX.	10	mA
dV/dt	V _D =540V Gate Open T _J =125		MIN.	40	V s
(dV/dt) _c	(dI/dt) _c =7.2A/ms, T	A _I Q _n		T	D

FIG.1: Maximum power dissipation versus RMS on-state current

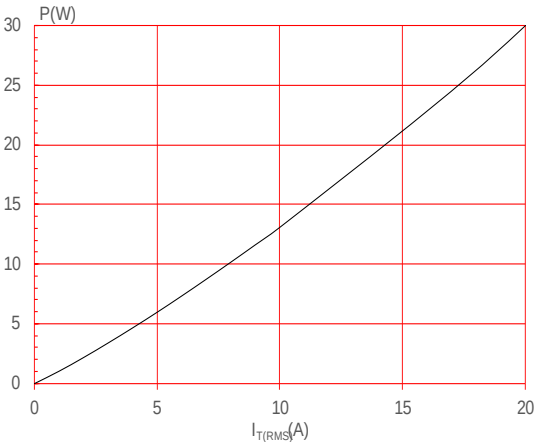


FIG.2: RMS on-state current versus case temperature



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

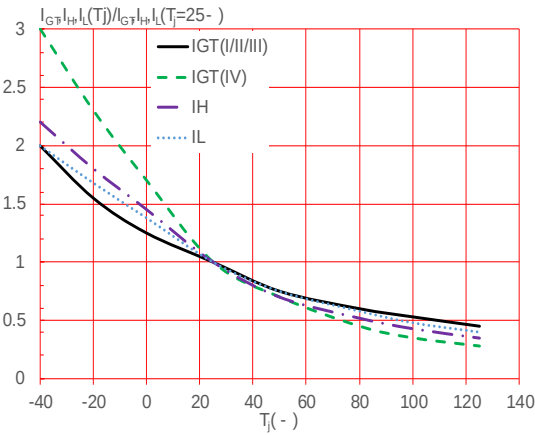


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H- I- J	K			
JST139E-800D	800	5	10	TO-263	50	Tube

PACKAGE MECHANICAL DATA

DELIVERY MODE



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